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Advanced Photonix, Inc. PDB-708

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### Distributor of Advanced Photonix, Inc.: Excellent Integrated System Limited

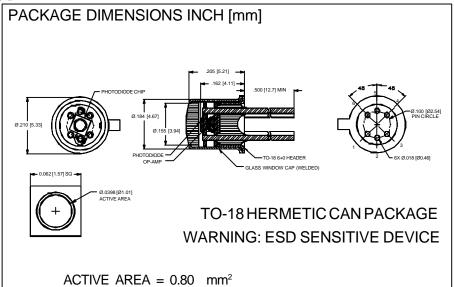
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Datasheet of PDB-708 - PHOTODIODE FIBER OPTIC TO-18

PHOTONIC DETECTORS INC.

# High Speed Detector Amplifier Hybrid Type PDB-708





#### **FEATURES**

- 24 MHz bandwidth
- single supply operation
- Wide dynamic range
- Low power: 5 V @ 25 mA

#### **DESCRIPTION**

The **PDB-708** is a high speed PIN photodiode integrated with a wide band differential output transimpedance amplifier. It is packaged in a TO-18, 6 leaded hermetic package. Options include, SMA, ST & FC type fiber optic ADMs.

#### PHOTODIODE ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

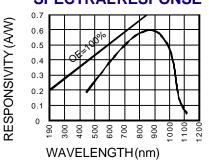
SYMBOL	PARAMETER	MIN	MAX	UNITS
VBR	Reverse Voltage		300	V
T <sub>STG</sub>	Storage Temperature	-55	+125	∘C
То	Operating Temperature Range	-40	+80	⊙C
Ts	Soldering Temperature*		+260	∘C
I <sub>L</sub>	Light Current		500	mA

<sup>\*1/16</sup> inch from case for 3 secs max

#### **APPLICATIONS**

- Fiber optic receivers
- Industrial controls
- High speed optical coupling
- Local area network

#### **SPECTRALRESPONSE**



#### PHOTODIODE ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	7	8.5		μΑ
ΙD	Dark Current	$H = 0, V_R = 10 V$		2	10	nA
RsH	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$		500		MΩ
TC RsH	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-8		%/℃
C₁	Junction Capacitance	$H = 0, V_R = 45 V^{**}$		2.2	2.4	pF
λrange	Spectral Application Range	Spot Scan	400		1100	nm
λр	Spectral Response - Peak	Spot Scan		900		nm
V <sub>BR</sub>	Breakdown Voltage	I = 1 μ.Α	100	300		V
NEP	Noise Equivalent Power	VR = 45 V @ Peak		1x10 <sup>-14</sup>		W/√ <sub>Hz</sub>
tr	Response Time	RL= $50\Omega V_R$ = $45 V\lambda$ = $900 nm$		3		nS



# PHOTONIC DETECTORS INC.

## High Speed Detector Amplifier Hybrid Type PDB-708

AMPLIFIER SPECIFICATION (SO PACKAGE @T\_a = 25° C and VS = +5 vdc UNLESS OTHERWISE NOTED

CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
DYNAMIC PERFORMANCE BANDWIDTH PULSE WIDTH MODULATION RISE AND FALL TIME SETTLING TIME	3 dB 10 µA TO 200 µA PEAK 10% TO 90% TO 3%, 0.5 V DIFF OUTPUT STEP	180	500 1.5 3		MHz ps ns ns
INPUT LINEAR INPUT CURRENT RANGE MAX INPUT CURRENT RANGE OPTICAL SENSITIVITY INPUT STRAY CAPACITANCE INPUT BIAS VOLTAGE	DIE, BY DESIGN SOIC, BY DESIGN +V <sub>S</sub> TO I <sub>N</sub> AND V <sub>BYP</sub>	±200	±30 ±350 -36 0.2 0.4	2.0	µµA µµA dBm pF pF V
INPUT CURRENT NOISE TOTAL INPUT RMS NOISE	DIE, SINGLE ENDED AT POUT, OR DIFFERENTIAL ( $P_{OUT}$ - $N_{OUT}$ ), $C_{STRAY} = 0.3  pF$ f = 100 MHz DC TO 100 MHz		3.0 26.5		pA/√ <del>Hz</del> nA
TRANSFER CHARACTERISTICS TRANSRESISTANCE  POWER SUPPLY REJECTION RATIO	SINGLE ENDED DIFFERENTIAL SINGLE ENDED DIFFERENTIAL	8 16	10 20 37.0 40	12 24	KΩ KΩ dB dB
OUTPUT DIFFERENTIAL OFFSET OUTPUT COMMON-MODE VOLTAGE VOLTAGE SWING (DIFFERENTIAL) OUTPUT IMPEDANCE	FROM POSITIVE SUPPLY POSITIVE INPUT CURRENT, $R_L = \infty$ POSITIVE INPUT CURRENT, $R_L = 50 \Omega$	-1.5 40	6 -1.3 1.0 600 50	20 -1.1	$\begin{array}{c} mV \\ V \\ V_{PP} \\ mV_{PP} \\ \end{array}$
POWERSUPPLY OPERATING RANGE CURRENT	T <sub>MIN</sub> TOT <sub>MAX</sub> SINGLE SUPPLY DUAL SUPPLY	+4.5 ±2.25	+5 25	+11 ±5.5 26	V V mA

#### AMPLIFIER ABSOLUTE MAXIMUM RATING (TA=25 ℃UNLESSOTHERWISE NOTED)

PARAMETER	MIN	MAX	UNITS
SUPPLYVOLTAGE	±4.5	±12	V
POWER DISSIPATION		.9	$\mu$ V
STORAGETEMPERATURE	-55	+125	° C
OPERATINGTEMPERATURE	-40	+85	° C

